L Number	Hits	Search Text	DB	Time stamp
2	0	(w tungsten) adj2 (silicon si) adj2 (n	USPAT;	2004/10/12 13:52
		nitride) near15 thick\$4 and semicondutor	US-PGPUB;	
		and (interconnect\$4 wiring wire\$	EPO; JPO	
i _		contact\$3)		
3	2	\",, \	USPAT;	2004/10/12 13:55
		nitride) and semicondutor and	US-PGPUB;	
1 .		(interconnect\$4 wiring wire\$ contact\$3)	EPO; JPO	
4	2	'	USPAT;	2004/10/12 13:54
		nitride) and semicondutor and	US-PGPUB;	
		(interconnect\$4 wiring wire\$ contact\$3))	EPO; JPO	
		and (w tungsten) adj2 (silicon si) adj2 (n		
_	0.4007.64	nitride)		
5	2408764	(w tungsten) adj\$4 (silicon si) adj\$4 (n	USPAT;	2004/10/12 13:56
		nitride) and semicondutor and	US-PGPUB;	
_	0400700	(interconnect\$4 wiring wire\$ contact\$3)	EPO; JPO	
6	2408720	((w tungsten) adj\$4 (silicon si) adj\$4 (n	USPAT;	2004/10/12 13:59
i		nitride) and semicondutor and	US-PGPUB;	1
}		(interconnect\$4 wiring wire\$ contact\$3))	EPO; JPO	
		and (w tungsten) adj\$4 (silicon si) adj\$4		
		(n nitride) near15 thick\$4 and		
		semicondutor and (interconnect\$4 wiring		
_	000000	wire\$ contact\$3)	[
7	2339790	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2004/10/12 14:01
		nitride) and semicondutor and	US-PGPUB;	
		(interconnect\$4 wiring wire\$ contact\$3))	EPO; JPO	
		and (w tungsten) adj\$3 (silicon si) adj\$3		
		(n nitride) near15 thick\$4 and		
		semicondutor and (interconnect\$4 wiring		
8	1973346	wire\$ contact\$3)		0004/10/10 11 00
0	19/3346	, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/10/12 14:02
		nitride) and semicondutor and	US-PGPUB;	
		(interconnect\$4 wiring wire\$ contact\$3))	EPO; JPO	
		and (w tungsten) adj\$2 (silicon si) adj\$2		
		(n nitride) near15 thick\$4 and		
		semicondutor and (interconnect\$4 wiring wire\$ contact\$3)		
9	32598		TICDAM.	2004/10/12 14:15
	32330	nitride) and semicondutor and	USPAT; US-PGPUB;	2004/10/12 14:15
	ŀ	(interconnect\$4 wiring wire\$ contact\$3))	EPO; JPO	
		and (w tungsten) adj\$2 (silicon si) adj\$2	210, 010	
		(n nitride) near15 thick\$4 and		
		semicondutor and (interconnect\$4 wiring		
		wire\$ contact\$3)) and (tungten adj silicon		
		adj nitride\$1 w adj si adj\$2 n) near15		
		thick\$4		
10	465	((((w tungsten) adj\$4 (silicon si) adj\$4	USPAT;	2004/10/12 14:06
		(n nitride) and semicondutor and	US-PGPUB;	
		(interconnect\$4 wiring wire\$ contact\$3))	EPO; JPO	
		and (w tungsten) adj\$2 (silicon si) adj\$2		
		(n nitride) near15 thick\$4 and		
		semicondutor and (interconnect\$4 wiring		
		wire\$ contact\$3)) and (tungten adj silicon		
		adj nitride\$1 w adj si adj\$2 n) near15		
		thick\$4) and grad\$3 near5 (tungten adj		
		silicon adj nitride\$1 w adj si adj\$2 n)		
11	465	(((((w tungsten) adj\$4 (silicon si) adj\$4	USPAT;	2004/10/12 14:08
		(n nitride) and semicondutor and	US-PGPUB;	
		(interconnect\$4 wiring wire\$ contact\$3))	EPO; JPO	
		and (w tungsten) adj\$2 (silicon si) adj\$2		
		(n nitride) near15 thick\$4 and		
		semicondutor and (interconnect\$4 wiring		
		wire\$ contact\$3)) and (tungten adj silicon		
		adj nitride\$1 w adj si adj\$2 n) near15		
		thick\$4) and grad\$3 near5 (tungten adj		
		silicon adj nitride\$1 w adj si adj\$2 n))		
		and grad\$3 near5 (tungten adj silicon adj		
	1	nitride\$1 w adj si adj\$2 n)	l	1

	,			
12	295	(((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semicondutor and (interconnect\$4 wiring wire\$ contact\$3))	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:11
		and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and (tungten adj silicon adj nitride\$1 w adj si adj\$2 n) near15 thick\$4) and grad\$3 near5 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n) and grad\$3 near3 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n) and grad\$3 near3 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n)		
13	15	(((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and (tungten adj silicon adj nitride\$1 w adj si adj\$2 n) near15 thick\$4) and grad\$3 near5 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n)) and barrier near10 grad\$3 near3 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n) n adj silicon adj nitride\$1 w adj si adj\$2 n)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:12
14	370021	(((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungten adj	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:17
16	1434	silicon w adj si) near15 thick\$4 ((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:20
		(n nitride) near15 thick\$4 and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungten adj silicon w adj si) near15 thick\$4) and diffusion near3 (barrier prevent\$3) near7 grad\$7 (tungten adj silicon w adj si)		
17	75	(((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungten adj silicon w adj si) near15 thick\$4) and diffusion near3 (barrier prevent\$3) near7 grad\$7 (tungten adj silicon w adj si) near7	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:31
19	0	nitrid\$5 ((((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semicondutor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungten adj silicon w adj si) near15 thick\$4) and diffusion poor3 (barrier propert\$3) near7	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:32
		diffusion near3 (barrier prevent\$3) near7 grad\$7 (tungten adj silicon w adj si)) and (tungten adj silicon w adj si) near7 nitrid\$5) and grad\$3 near7 (tungten adj silicon w adj si) near7 nitrid\$5		

20	0 (((((w tungsten) adj\$4 (silicon si) adj\$4	USPAT;	2004/10/12 14:33
	(n nitride) and semicondutor and	US-PGPUB;	
	(interconnect\$4 wiring wire\$ contact\$3))	EPO; JPO	
	and (w tungsten) adj\$2 (silicon si) adj\$2		
	(n nitride) near15 thick\$4 and		
•	semicondutor and (interconnect\$4 wiring		
	wire\$ contact\$3)) and grad\$7 (tungten adj		
	silicon w adj si) near15 thick\$4) and		
	diffusion near3 (barrier prevent\$3) near7		
	grad\$7 (tungten adj silicon w adj si))		
	and (tungten adj silicon w adj si) near7		
	nitrid\$5) and grad\$5 near7 (tungten adj		
	silicon w adj si) near7 nitrid\$5		.